

YJ Planar Schottky Barrier Diode Die Specification

100V 3A, 50mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB050S100SS-280A

Main Products Characterstics

- Average forward current: $I_F(AV) = 3\text{ A}$
- Maximum operating junction temperature: $T_j = 175\text{ }^{\circ}\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Static Electrical Characteristics ($T_a = 25^{\circ}\text{C}$)

$I_F = 3\text{ A}$
Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice